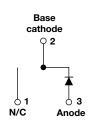
VS-HFA08TB120S-M3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 8 A



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PRIMARY CHARACTERISTICS						
I _{F(AV)}	8 A					
V _R	1200 V					
V _F at I _F	2.4 V					
t _{rr} (typ.)	28 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- \bullet Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	8				
Single pulse forward current	I _{FSM}		130	А			
Maximum repetitive forward current	I _{FRM}		32				
Movimum neuror dissinction	PD	T _C = 25 °C	73.5	W			
Maximum power dissipation		T _C = 100 °C	29	- vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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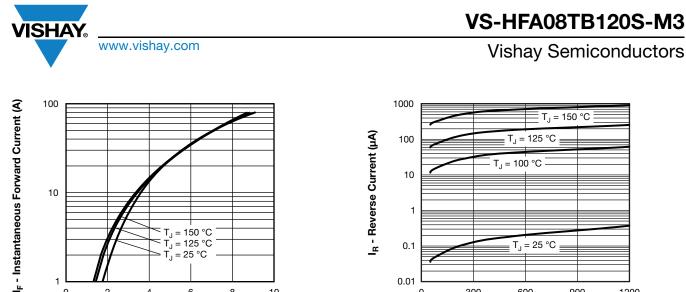
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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS				TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-			
Maximum forward voltage		I _F = 8.0 A	-	2.6	3.3	v		
	V _{FM}	I _F = 16 A	-	3.4	4.3			
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1			
Maximum reverse Ieakage current		$V_{R} = V_{R}$ rated	-	0.31	10			
		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA		
Junction capacitance	CT	V _R = 200 V	-	11	20	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	A/μs, V _R = 30 V	-	28	-		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns	
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	106	160		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A nC	
Fear recovery current	I _{RRM2}	T _J = 125 °C		-	6.2	11		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380		
Peak rate of fall of recovery current during t _b	Q _{rr2}	T _J = 125 °C		-	335	880		
	dl _{(rec)M} /dt1	T _J = 25 °C]	-	133	-	A∕µs	
	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-	λγµs	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	к/w			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	N/ VV			
Weight			-	2.0	-	g			
weigin			-	0.07	-	oz.			
Marking device		Case style D ² PAK (TO-263AB)	HFA08TB120S						



0 2 6 10 4 8 V_{FM} - Forward Voltage Drop (V)

Fig. 1 - Maximum Forward Voltage Drop Characteristics

1

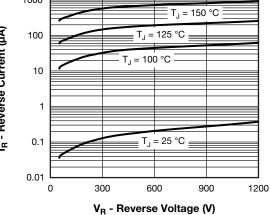


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

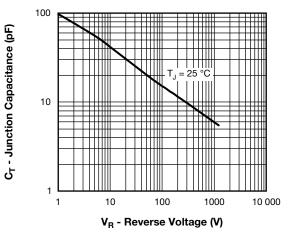


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

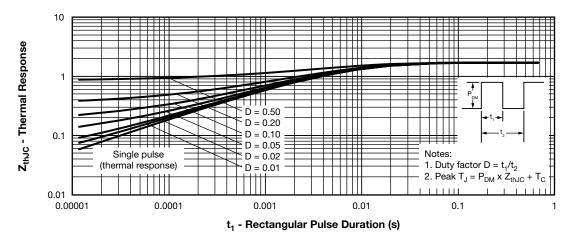


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



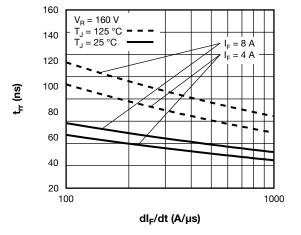


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

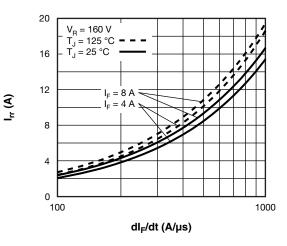


Fig. 6 - Typical Recovery Current vs. dl_F/dt

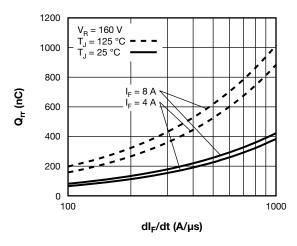


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)



Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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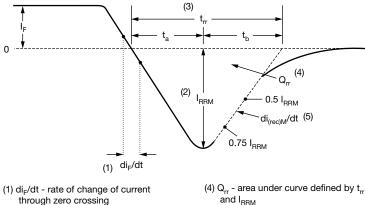
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(2) I_{BBM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

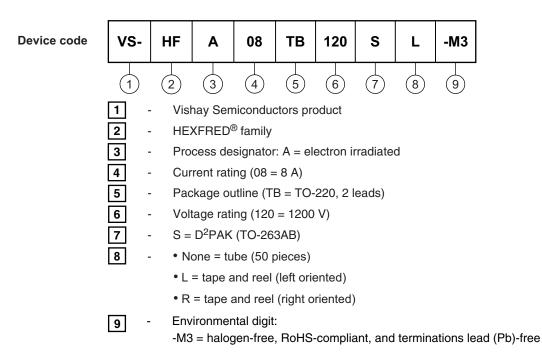
and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE





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ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08TB120S-M3	50	Antistatic plastic tube				
VS-HFA08TB120SR-M3	800	13" diameter reel				
VS-HFA08TB120SL-M3	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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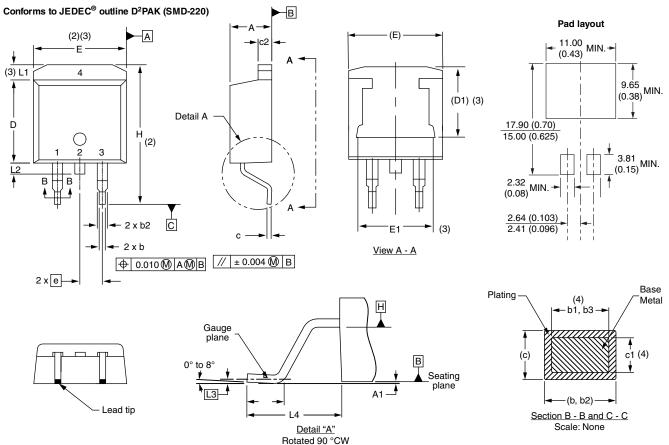
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D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INCHES		NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC) BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

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